# onsemi

# **MOSFET** – Power, Single N-Channel, Small Signal, SOT-23 60 V, 5.11 A

# NVRGS055N06CL

#### Features

- Low R<sub>DS(on)</sub>
- Small Footprint Surface Mount Package
- Trench Technology
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

					-
Paran	Symbol	Value	Unit		
Drain-to-Source Voltag	V <sub>DSS</sub>	60	V		
Gate-to-Source Voltage	e		V <sub>GS</sub>	±20	V
Continuous Drain		T <sub>L</sub> = 25°C	۱ <sub>D</sub>	5.11	А
Current R <sub>θJL</sub>	Steady	T <sub>L</sub> = 100°C		3.61	
Power Dissipation	State	T <sub>L</sub> = 25°C	PD	2.42	W
$R_{ hetaJL}$		T <sub>L</sub> = 100°C		1.21	
Continuous Drain	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	4.02	А
Current $R_{\theta JA}$		$T_A = 100^{\circ}C$		2.84	
Power Dissipation		T <sub>A</sub> = 25°C	PD	1.50	W
$R_{ heta JA}$		$T_A = 100^{\circ}C$		0.75	
Pulsed Drain Current	T <sub>A</sub> = 25	°C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	116	А
Operating Junction and Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C		
Source Current (Body D	I <sub>S</sub>	2.02	А		
Lead Temperature for So (1/8" from case for 10 s)	ΤL	260	°C		

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

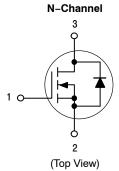
Characteristic	Symbol	Мах	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\thetaJA}$	100	°C/W
Junction-to-Lead - Steady State (Notes 1, 2)	$R_{\theta JL}$	62	

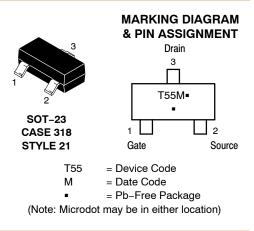
1. device mounted to 1 inch<sup>2</sup> 1s2p 2 oz copper

2. lead temp is referenced at the top of the drain pin

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX
60 V	70 mΩ @ 4.5 V 5.11 A	
00 V	51 mΩ @ 10 V	

#### **Simplified Schematic**





#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NVRGS055N06CLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

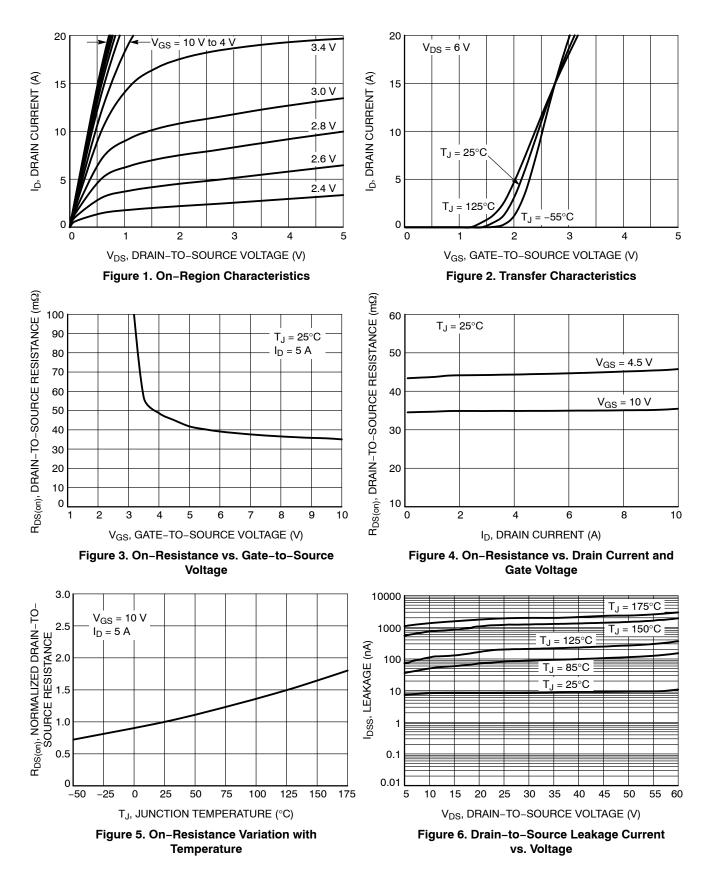
Parameter	Symbol	Test Co	ondition	Min	Тур	Max	Units
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, I <sub>D</sub> = 250 $\mu$ A		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>				24		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 60 V	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C			10 250	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>		V <sub>GS</sub> = 20 V			100	nA
ON CHARACTERISTICS (Note 3)		•					
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub>	, I <sub>D</sub> = 13 μA	1.2		2.2	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-5.5		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = 10 V, I <sub>D</sub> = 5 A $V_{GS}$ = 4.5 V, I <sub>D</sub> = 5 A			35	51	mΩ
					45	70	1
Forward Transconductance	<b>9</b> FS	V <sub>DS</sub> = 6 V, I <sub>D</sub> = 5 A			15.2		S
CHARGES AND CAPACITANCES	_	-			-	-	-
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V			344		pF
Output Capacitance	C <sub>OSS</sub>				173		
Reverse Transfer Capacitance	C <sub>RSS</sub>				5.0		1
Total Gate Charge	Q <sub>G(TOT)</sub>				6.1		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 48 V;		0.7		
Gate-to-Source Charge	Q <sub>GS</sub>	$I_D = 5 A$			1.2		
Gate-to-Drain Charge	Q <sub>GD</sub>				0.7		
SWITCHING CHARACTERISTICS, $V_{GS}$	= V (Note 4)	-			-	-	-
Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 5 A, R <sub>G</sub> = 1 Ω			5.0		ns
Rise Time	tr				1.6		1
Turn-Off Delay Time	t <sub>d(OFF)</sub>				12		
Fall Time	t <sub>f</sub>				1.7		1
DRAIN-SOURCE DIODE CHARACTER	ISTICS	•		-	-		-
Forward Diode Voltage	V <sub>SD</sub>	$V_{OO} = 0 V$	T <sub>J</sub> = 25°C		0.89	1.2	V

Diode Voltage  $\begin{array}{l} V_{GS}=0 \text{ V,} \\ I_{S}=5 \text{ A} \end{array}$ vsD  $T_J = 125^{\circ}C$ 0.78

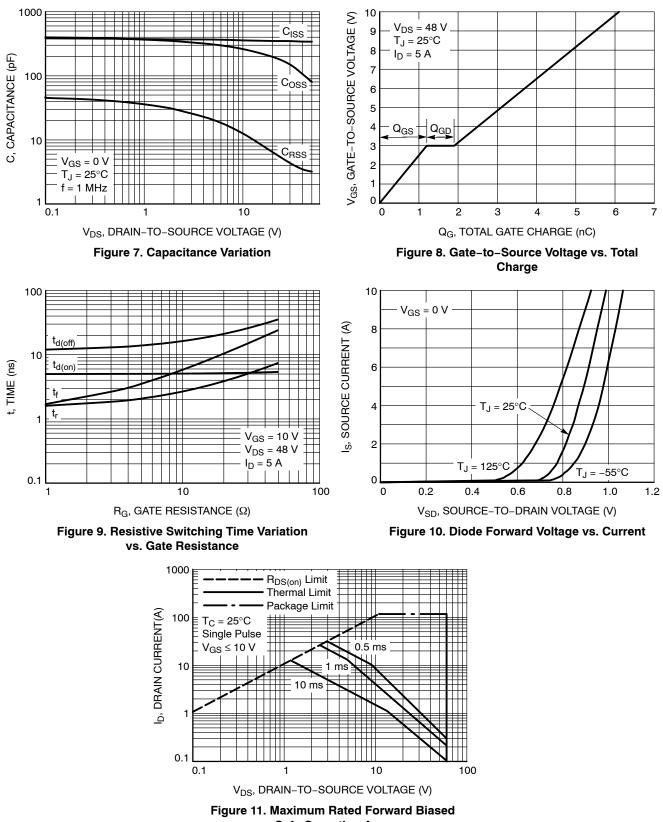
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2% 4. Switching characteristics are independent of operating junction temperatures

#### **TYPICAL CHARACTERISTICS**



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Safe Operating Area

#### **TYPICAL CHARACTERISTICS**

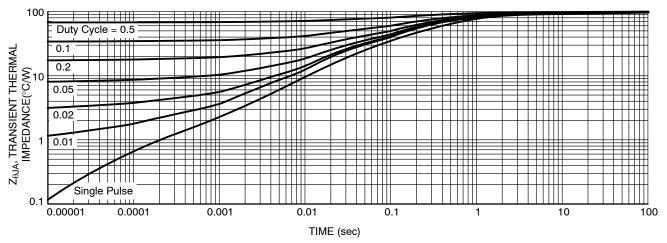
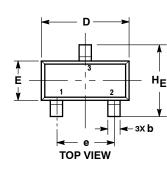
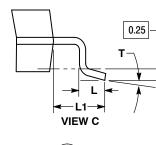


Figure 12. Thermal Response

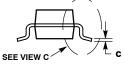
#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 









END VIEW

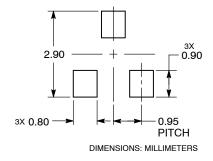
- NOTES:
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4 PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
Г	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
ΗE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 21	I:
PIN 1.	GATE
2.	SOU

SOURCE 3 DRAIN

#### RECOMMENDED SOLDERING FOOTPRINT



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